

Fig. 1

HOGAN & HARTSON – 81784.0293 WAKUI, et al., "Method for Manufacturing A Semiconductor Device..." EV 324 111 049 US Page 2 of 6

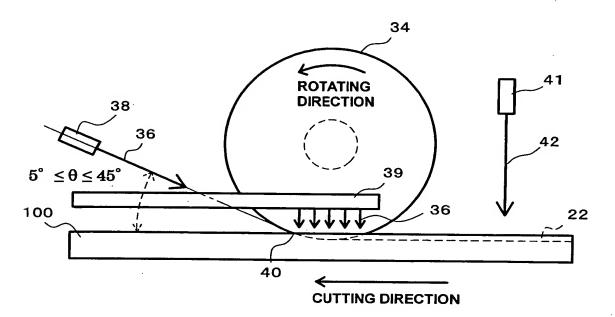


Fig. 2A

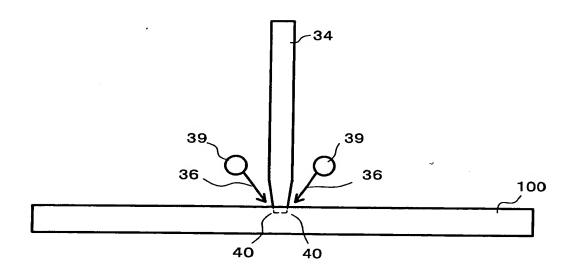


Fig. 2B

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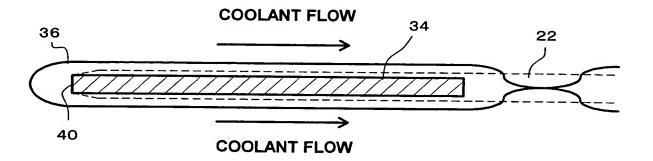


Fig. 3A

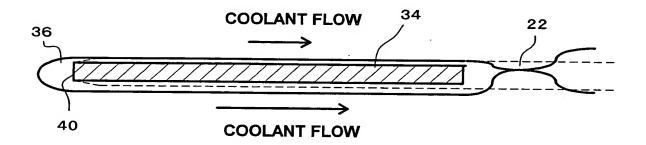


Fig. 3B

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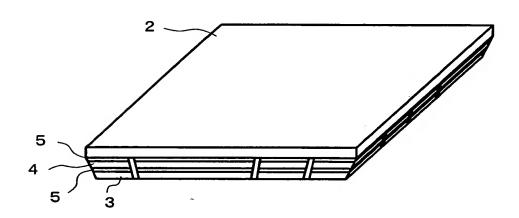


Fig. 4A

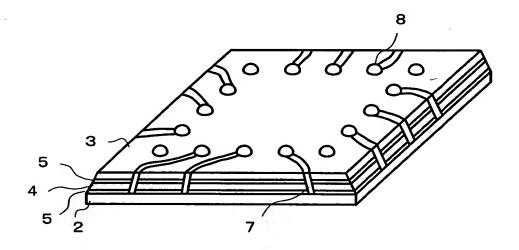


Fig. 4B

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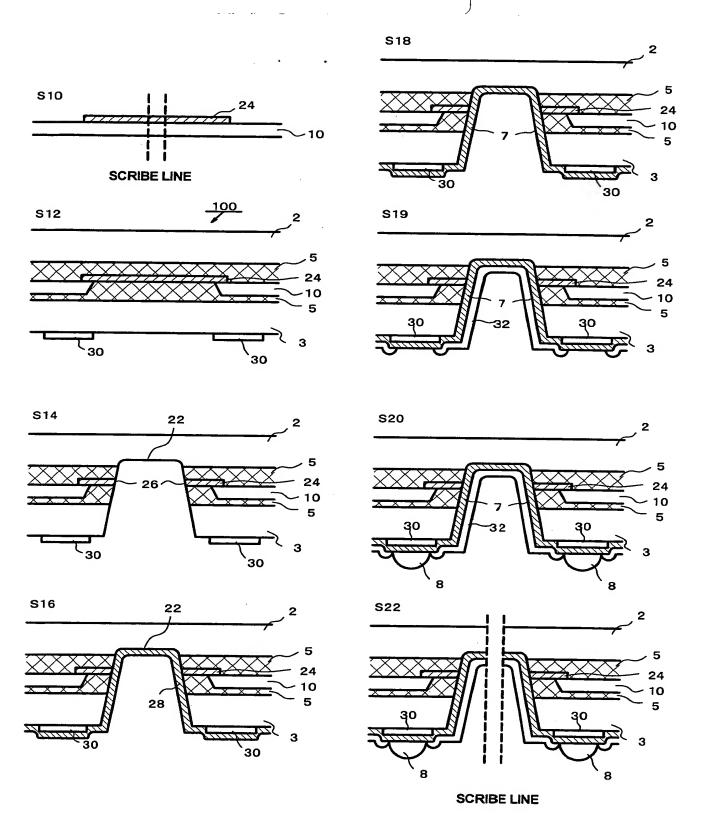


Fig. 5

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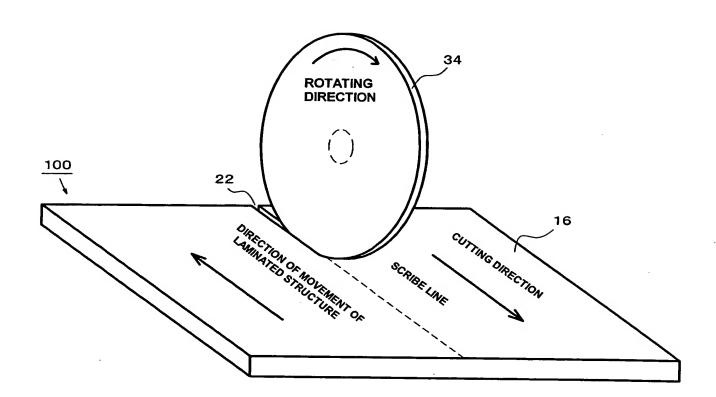


Fig. 6

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ShellOP

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On this page you can view the process flow of Shellcase's ShellOP pr duct.

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Step B: Glass 1 Attachment

Step C: Backside Silicon Grinding & Scribe Line Etch

Step D: Glass 2 Attachment

Step E: Compliant Layer Formation

Step F: Notch

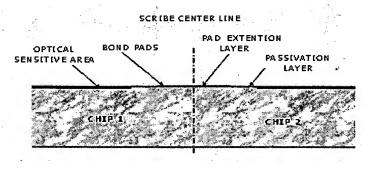
Step G: External Lead Formation

Step H: External Passivation

Step I: BGA Formation

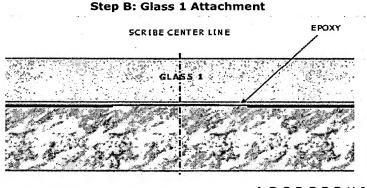
Step J: Dicing

Step A: Passivation and Pad Extension Layers



A B C D E F G H I J

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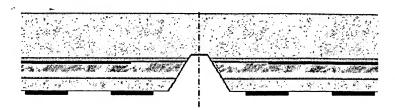


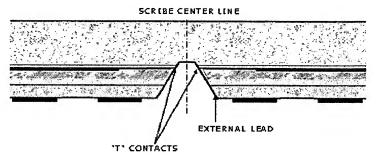
A B C D E F G H I J

Back (Next (Back to Top Step C: Backside Silic n Grinding & Scribe Line Etch SCRIBE CENTER LINE A B C D E F G H I J Back to Top Back (Next (Step D: Glass 2 Attachment SCRIBE CENTER LINE EPOXY A B C D E F G H I J Back to Top Back (1) flext() **Step E: Compliant Layer Formation** SCR (BE CENTER LINE COMPLIANT LAYER A B C D E F G H I J Back to Top Back (Next (Step F: Notch A B C D E F G H I J Back to Top Back (next)

Step G: External Lead F rmati n

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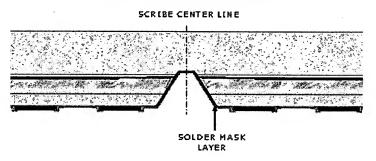


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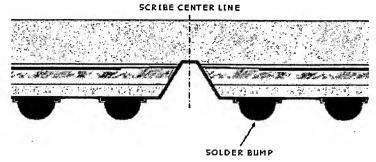
Step H: External Passivation



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Step I: BGA Formation

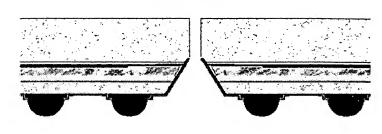


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Step J: Dicing

SCRIBE CENTER LINE



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